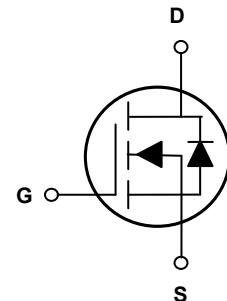
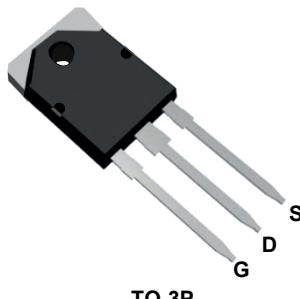


Main Product Characteristics

$V_{(BR)DSS}$	600V
$R_{DS(ON)}$	73mΩ (max.)
I_D	48A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSJV60R073 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Parameter	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-to-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current, @ Steady-State ($T_c=25^\circ\text{C}$)	I_D	48	A
Continuous Drain Current, @ Steady-State ($T_c=100^\circ\text{C}$)		30	A
Pulsed Drain Current	I_{DM}	192	A
Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	415	W
		3.32	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ¹	E_{AS}	2650	mJ
Single Pulse Current	I_{AS}	12.4	A
Body Diode Reverse Voltage Slope ²	dv/dt	15	V/ns
MOS dv/dt Ruggedness ³	dv/dt	50	V/ns
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Junction-to-Case	$R_{\theta JC}$	0.30	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to + 150	$^\circ\text{C}$
Soldering Temperature	T_{sold}	260	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	600	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=600\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	1.0	μA
		$V_{\text{DS}}=600\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	-	2.0	-	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=30\text{V}$	-	-	100	nA
		$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=-30\text{V}$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_D=22\text{A}$	-	65	73	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	2.0	-	4.0	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=100\text{V}, f=1\text{MHz}$	-	3082	-	pF
Output Capacitance	C_{oss}		-	171	-	
Reverse Transfer Capacitance	C_{rss}		-	9.4	-	
Total Gate Charge ^{4,5}	Q_g	$I_D=47\text{A}, V_{\text{DD}}=480\text{V}, V_{\text{GS}}=10\text{V}$	-	96	-	nC
Gate-to-Source Charge ^{4,5}	Q_{gs}		-	22	-	
Gate-to-Drain ("Miller") Charge ^{4,5}	Q_{gd}		-	48	-	
Gate Plateau ^{4,5}	V_{plateau}		-	6.3	-	V
Turn-On Delay Time ^{4,5}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=380\text{V}, V_{\text{GS}}=10\text{V}, R_G=1.8\Omega, I_D=47\text{A}$	-	23	-	nS
Rise Time ^{4,5}	t_r		-	32	-	
Turn-Off Delay Time ^{4,5}	$t_{\text{d}(\text{off})}$		-	86	-	
Fall Time ^{4,5}	t_f		-	24	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	2.1	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	$T_C=25^\circ\text{C}$, MOSFET symbol showing the integral reverse p-n junction diode.	-	-	48	A
Diode Pulse Current	$I_{\text{S,pulse}}$		-	-	192	A
Diode Forward Voltage	V_{SD}	$I_S=22\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.4	V
Reverse Recovery Time ⁴	T_{rr}	$I_S=22\text{A}, V_{\text{GS}}=0\text{V}, \frac{dI_F}{dt}=100\text{A/us}$	-	576	-	nS
Reverse Recovery Charge ⁴	Q_{rr}		-	14	-	μC
Reverse Recovery Peak Current ⁴	I_{rrm}		-	44	-	A

Note:

1. $L=30\text{mH}, V_{\text{DD}}=100\text{V}, R_G=25\Omega$, starting temperature $T_J=25^\circ\text{C}$.
2. $V_{\text{DS}}=0\text{-}400\text{V}, I_{\text{SD}} \leq I_S, T_J=25^\circ\text{C}$.
3. $V_{\text{DS}}=0\text{-}480\text{V}$.
4. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
5. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

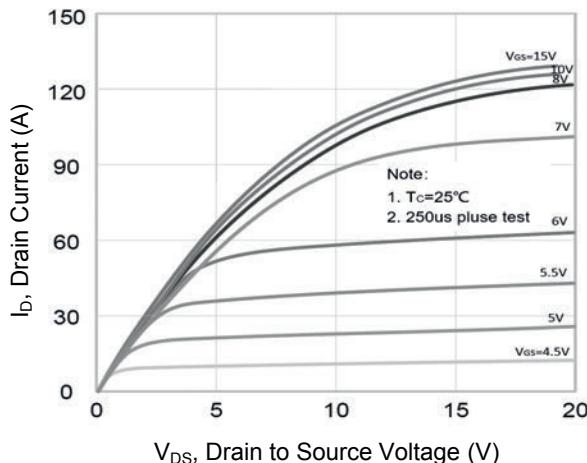


Figure 1. Typical Output Characteristics

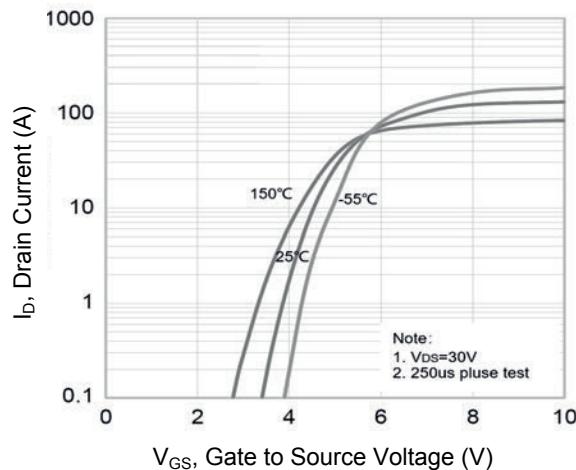


Figure 2. Transfer Characteristics

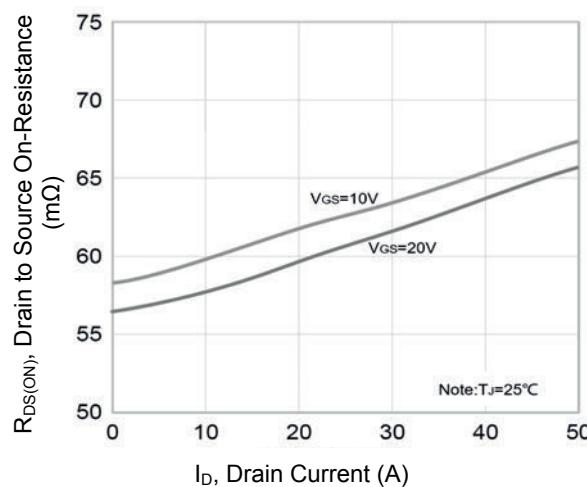


Figure 3. $R_{DS(ON)}$ Vs. Drain Current

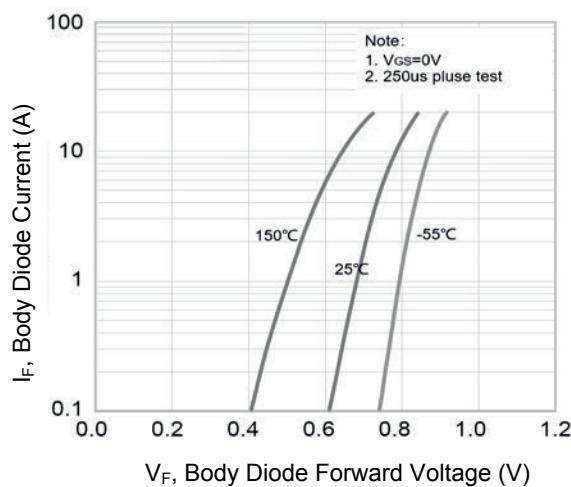


Figure 4. Body Diode Characteristics

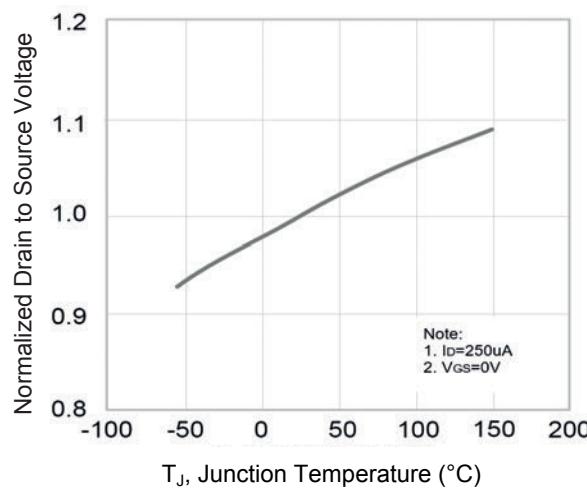


Figure 5. Normalized BV_{DSS} Vs. T_J

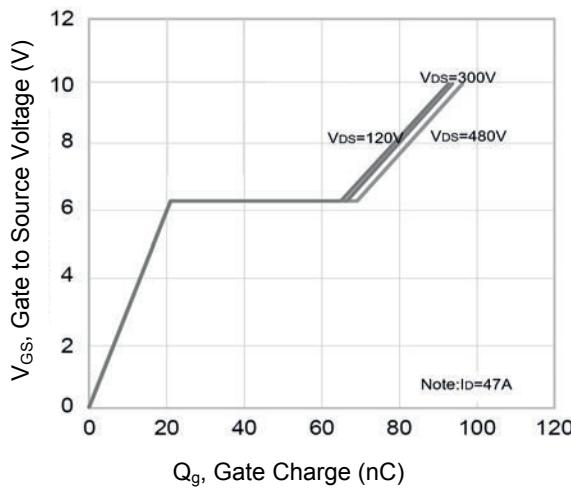


Figure 6. Gate Charge Characteristics

Typical Electrical and Thermal Characteristic Curves

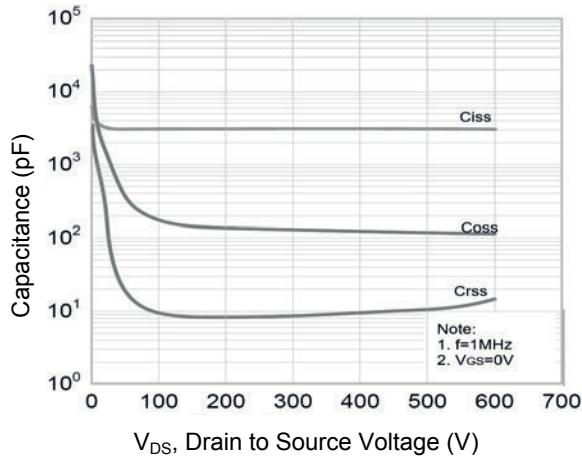


Figure 7. Capacitance Characteristics

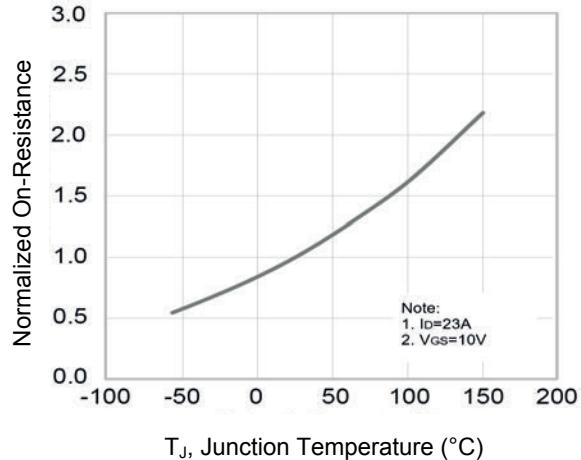


Figure 8. Normalized $R_{DS(ON)}$ Vs. T_J

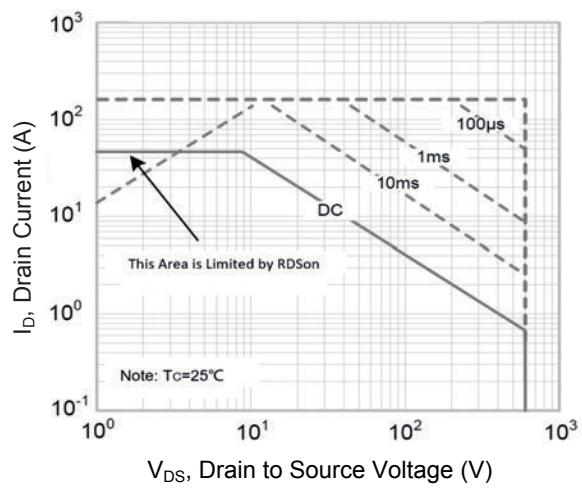
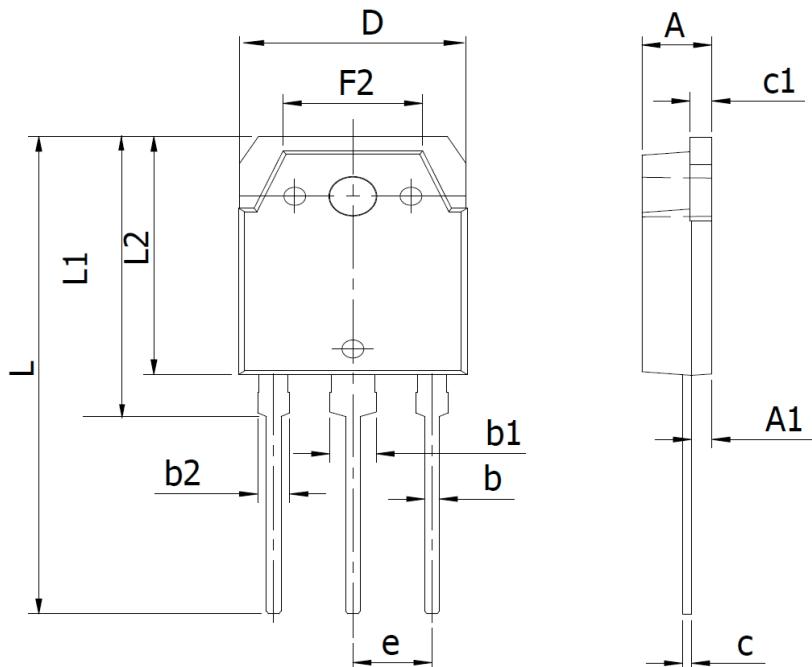


Figure 9. Safe Operation Area

Package Outline Dimensions (TO-3P)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	5.20	0.173	0.205
C1	1.20	1.80	0.047	0.071
A1	1.20	2.00	0.047	0.079
b	0.70	1.30	0.028	0.051
b1	2.70	3.30	0.106	0.130
b2	1.70	2.30	0.067	0.091
D	15.00	16.00	0.591	0.630
C	0.40	0.80	0.016	0.031
F2	8.50	10.00	0.335	0.394
e	5.45 TYP		0.215 TYP	
L1	22.60	23.60	0.890	0.929
L	39.00	41.50	1.535	1.634
L2	19.50	21.00	0.768	0.827